



DMN2005DLP4K

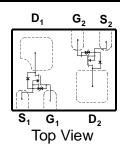
DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

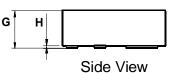
Features

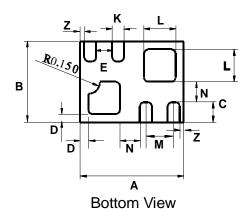
- Low On-Resistance
- Very Low Gate Threshold Voltage, 0.9V Max.
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 4)
- **ESD Protected Gate**
- **Ultra Low Profile Package**

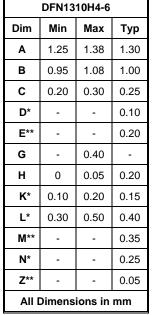
Mechanical Data

- Case: DFN1310H4-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking: See Page 4
- Ordering & Date Code Information: See Page 4









Dimensions D, K, L, N Repeat 4X Dimensions E, M, Z Repeat 2X



Maximum Ratings @T_A = 25°C unless otherwise specified

| Characteristic | | Symbol | Value | Unit |
|---|-------------------------------|------------------------------------|-------------|------|
| Drain-Source Voltage | | V _{DSS} | 20 | V |
| Gate-Source Voltage | | V _{GSS} | ±10 | V |
| Drain Current per element (Note 1) | Continuous Pulsed (Note 3) | I _D | 200 250 | mA |
| Total Power Dissipation (Note 1) | | P _d | 350 | mW |
| Thermal Resistance, Junction to Ambient | | $R_{\scriptscriptstyle{\thetaJA}}$ | 357 | °C/W |
| Operating and Storage Temperature Range |) | T _i , T _{STG} | -65 to +150 | °C |

Notes:

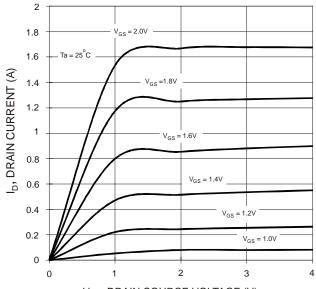
- 1. Device mounted on FR-4 PCB.
- 2. No purposefully added lead.
- Pulse width ${\leq}10\mu S,$ Duty Cycle ${\leq}1\%.$
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.



Electrical Characteristics @T_A = 25°C unless otherwise specified

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition |
|--|----------------------|--------------|----------------------------------|---------------------------------|------|---|
| OFF CHARACTERISTICS (per element) (Note 5) | • | | | • | • | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 20 | _ | _ | V | $V_{GS} = 0V, I_D = 100 \mu A$ |
| Zero Gate Voltage Drain Current | I _{DSS} | _ | _ | 10 | μА | $V_{DS} = 17V, V_{GS} = 0V$ |
| Gate-Source Leakage | I _{GSS} | _ | _ | ±5 | μА | $V_{GS} = \pm 8V$, $V_{DS} = 0V$ |
| ON CHARACTERISTICS (per element) (Note 5) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | 0.53 | _ | 0.9 | V | $V_{DS} = V_{GS}$, $I_D = 100 \mu A$ |
| Static Drain-Source On-Resistance | R _{DS (ON)} | | 0.9 0.85 1.2 2.4 2.5 | 1.5 1.7 1.7 3.5 3.5 | Ω | $\begin{split} &V_{GS} = 4V, \ I_D = 10 \text{mA} \\ &V_{GS} = 2.7V, \ I_D = 200 \text{mA} \\ &V_{GS} = 2.5V, \ I_D = 10 \text{mA} \\ &V_{GS} = 1.8V, \ I_D = 200 \text{mA} \\ &V_{GS} = 1.5V, \ I_D = 1 \text{mA} \end{split}$ |
| Forward Transfer Admittance | Y _{fs} | 40 | _ | _ | mS | $V_{DS} = 3V$, $I_D = 10mA$ |

Notes: 5. Short duration test pulse used to minimize self-heating effect.



V_{DS}, DRAIN-SOURCE VOLTAGE (V) Fig. 1 Typical Output Characteristics

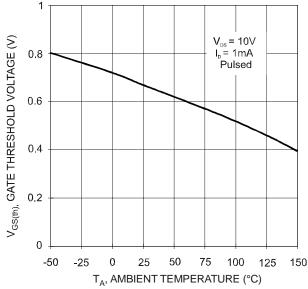


Fig. 3 Gate Threshold Voltage vs. Ambient Temperature

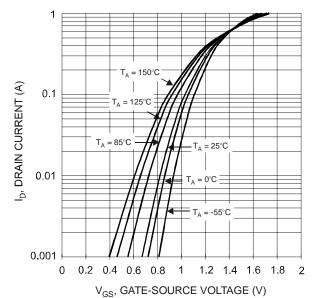


Fig. 2 Reverse Drain Current vs. Source-Drain Voltage

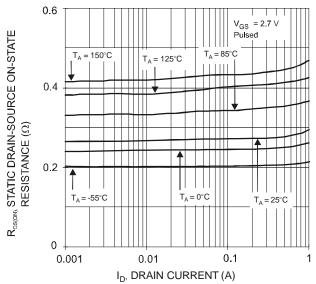


Fig. 4 Static Drain-Source On-State Resistance vs. Drain Current



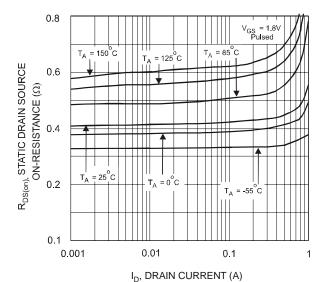


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

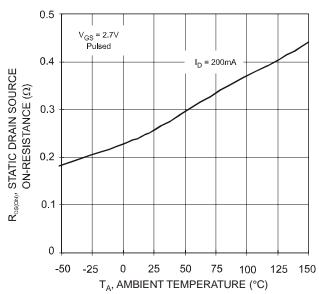


Fig. 7 Static Drain-Source, On-Resistance vs. Ambient Temperature

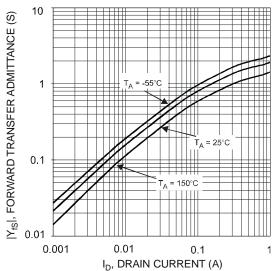
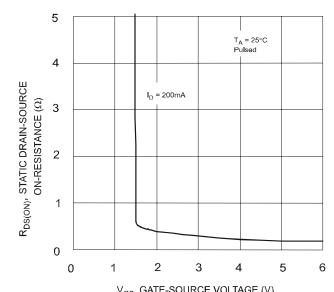
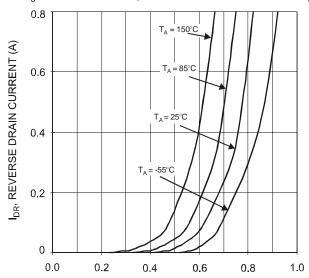


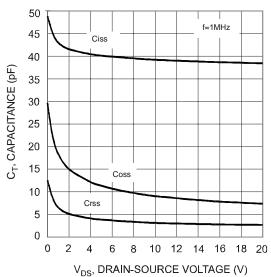
Fig. 9 Forward Transfer Admittance vs. Drain Current



 $\label{eq:VGS} V_{GS}, \, \text{GATE-SOURCE VOLTAGE (V)}$ Fig. 6 Static Drain-Source, On-Resistance vs. Gate-Source Voltage



 $\label{eq:VSD} {\rm V_{SD,}} \ {\rm DRAIN\text{-}SOURCE} \ {\rm VOLTAGE} \ ({\rm V})$ Fig. 8 Reverse Drain Current vs. Source-Drain Voltage



V_{DS}, DRAIN-SOURCE VOLTAGE (V₎ Fig. 10 Typical Capacitance



Ordering Information (Note 6)

| Device | Packaging | Shipping |
|----------------|-------------|------------------|
| DMN2005DLP4K-7 | DFN1310H4-6 | 3000/Tape & Reel |

Notes: For packaging details, please go to our website at http://www.diodes.com/ap02007.pdf.

Marking Information

DL

DL = Product Type Marking Code

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